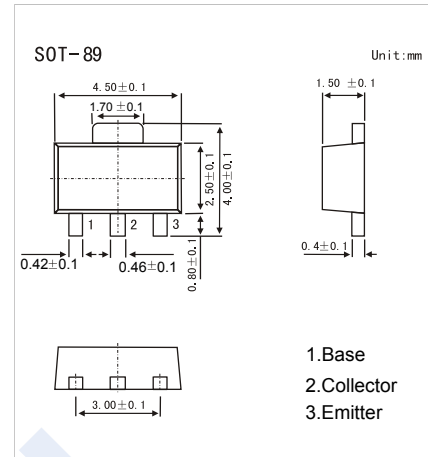


NPN Transistors

BF622 (KF622)

■ Features

- Low current
- High voltage

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	250	V
Collector - Emitter Voltage	V_{CE0}	250	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_c	50	mA
Collector Power Dissipation	P_c	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100 \mu\text{A}, I_E = 0$	250			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 1 \text{ mA}, I_B = 0$	250			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}, I_c = 0$	5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 200 \text{ V}, I_E = 0$			100	nA
Emitter cut-off current	I_{EB0}	$V_{EB} = 5 \text{ V}, I_c = 0$			50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 30 \text{ mA}, I_B = 5 \text{ mA}$			0.6	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 30 \text{ mA}, I_B = 5 \text{ mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 20 \text{ V}, I_c = 25 \text{ mA}$	50			
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_c = 10 \text{ mA}, f = 100 \text{ MHz}$	60			MHz

■ Marking

Marking	DA
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